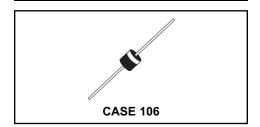
CR6A2GPP CR6A8GPP CR6A4GPP CR6A10GPP

CR6A6GPP

**GLASS PASSIVATED JUNCTION GENERAL PURPOSE SILICON RECTIFIER** 6A, 200 THRU 1000 VOLTS





## **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CR6A4GPP Series types are 6.0 Amp Glass Passivated Junction Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for use in all types of military, commercial, industrial, entertainment, computer, and automotive applications.

THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.

MARKING: FULL PART NUMBER

<b>MAXIMUM RATINGS</b> : (T <sub>A</sub> =25°C unless otherwise noted)			<u>CR6A</u>					
	SYMBOL	2GPP	4GPP	6GPP	8GPP	<u>10GPP</u>	UNITS	
Peak Repetitive Reverse Voltage	$V_{RRM}$	200	400	600	800	1000	V	
DC Blocking Voltage	$V_{R}$	200	400	600	800	1000	V	
RMS Reverse Voltage	V <sub>R(RMS)</sub>	140	280	420	560	700	V	
Non-Repetitive Peak Reverse Voltage (Halfwave, single phase, 60Hz peak)	V <sub>RSM</sub>	240	480	720	960	1200	V	
Average Forward Current, T <sub>A</sub> =60°C	IO			6.0			Α	
Non-Repetitive Peak Forward Surge Current (Halfwave, single phase, 60Hz peak)	IFSM			400			Α	
Operating and Storage Junction Temperature	$T_{\rm I}, T_{\rm sta}$		-6	65 to +17	<b>'</b> 5		°C	

**ELECTRICAL CHARACTERISTICS**: (T<sub>A</sub>=25°C unless otherwise noted))

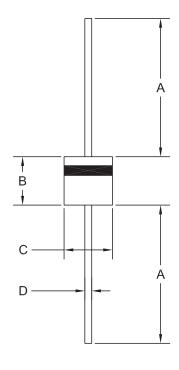
SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
$I_{R}$	V <sub>R</sub> =Rated V <sub>RRM</sub>	10	μΑ	
$I_{R}$	V <sub>R</sub> =Rated V <sub>RRM</sub> , T <sub>A</sub> =100°C	1.0	mA	
٧E	I <sub>⊏</sub> =6.0A	1.0	V	



CR6A2GPP CR6A4GPP CR6A6GPP

## GLASS PASSIVATED JUNCTION GENERAL PURPOSE SILICON RECTIFIER 6A, 200 THRU 1000 VOLTS

## **CASE 106 - MECHANICAL OUTLINE**



R1

DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
Α	1.000	-	25.40	-				
В	0.340	0.360	8.64	9.14				
С	0.340	0.360	8.64	9.14				
D	0.048	0.053	1.22	1.35				

CASE 106 (REV: R1)

MARKING: FULL PART NUMBER